

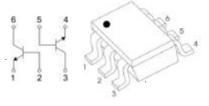


# Product data sheet

www.msksemi.com







SOT-363

#### DUAL TRANSISTOR (NPN+NPN)

#### APPLICATION

This device is designed for general purpose amplifier applications

#### MARK:1Ft

#### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
Vсво	Collector-Base Voltage	50		
VCEO	Collector-Emitter Voltage 45		V	
Vebo	Emitter-Base Voltage	6		
lc	Collector Current-Continuous	100	mA	
PD	Power Dissipation	200	mW	
Reja	Thermal Resistance. Junction to Ambient	625	°C/W	
Tj	Junction Temperature	150		
Tstg	Storage Temperature Range	-55~+150	°C	

#### **ELECTRICAL CHARACTERISTICS (T**<sub>a</sub>=25℃ unless otherwise specified)

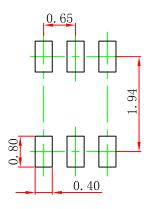
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	lc=10µA,I⊨=0	50			V
Collector-emitter breakdown voltage	V(BR)CEO	Ic=1mA,IB=0	45			V
Emitter-base breakdown voltage	V(BR)EBO	I <sub>E</sub> =10μA,I <sub>C</sub> =0	6			V
Collector cut-off current	Ісво	V <sub>CB</sub> =30V,I <sub>E</sub> =0			15	nA
Emitter cut-off current	Іево	VEB =4V, Ic=0			15	ΠA
DC current gain*	h <sub>FE</sub>	V <sub>CE</sub> =5V,Ic=2mA A	110		220	
		E	200		450	
		C	420		800	
	VCE(sat)(1)	Ic=10mA,I <sub>B</sub> =0.5mA			0.25	V
Collector-emitter saturation voltage	VCE(sat)(2)	lc=100mA,I <sub>B</sub> =5mA			0.65	V
Descentification in the second	VBE(1)	V <sub>CE</sub> =5V,Ic=2mA	0.58		0.7	V
Base-emitter voltage	VBE(2)	V <sub>CE</sub> =5V,Ic=10mA			0.77	V
Transition frequency	fτ	V <sub>CE</sub> =5V,Ic=20mA ,f=100MHz		200		MHz
Collector output capacitance	Cob	V <sub>CB</sub> =10V,I <sub>E</sub> =0,f=1MHz		2		pF

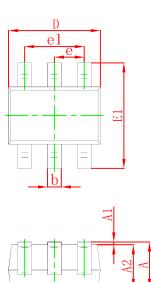
\*pulse test: Pulse Width  $\leq$ 300µs, Duty Cycle $\leq$  2.0%.





SOT-363

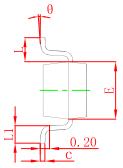




Note:

1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.



Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
С	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
е	0.650	) TYP	0.020	6 TYP
e1	1.200	1.400	0.047	0.055
L	0.525	5 REF	0.02	REF
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

### **REEL SPECIFICATION**

P/N	PKG	QTY
BC847S	SOT-363	3000





## <u>Attention</u>

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications f any and all MSKSEMI Semiconductor products described orcontained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuits for safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by MSKSEMI manufacturer:

Other Similar products are found below :

BC559C MCH4017-TL-H MMBT-2369-TR BC546/116 NJVMJD148T4G NTE16 NTE195A IMX9T110 2N4401-A 2N4403 2N6728 2SA1419T-TD-H 2SA2126-E 2SB1204S-TL-E FMC5AT148 2N2369ADCSM 2N2907A 2N3904-NS 2N5769 2SC4618TLN CPH6501-TL-E MCH4021-TL-E Jantx2N5416 US6T6TR BAX18/A52R BC556/112 IMZ2AT108 MMST8098T146 UMX21NTR MCH6102-TL-E TTA1452B,S4X(S 2N3879 NTE13 NTE282 NTE323 NTE350 NTE81 JANTX2N2920L JANTX2N3735 JANSR2N2222AUB CMLT3946EG TR SNSS40600CF8T1G CMLT3906EG TR GRP-DATA-JANS2N2907AUB GRP-DATA-JANS2N2222AUA MMDT3946FL3-7 2N4240 JANS2N3019 MSB30KH-13 2N2221AUB